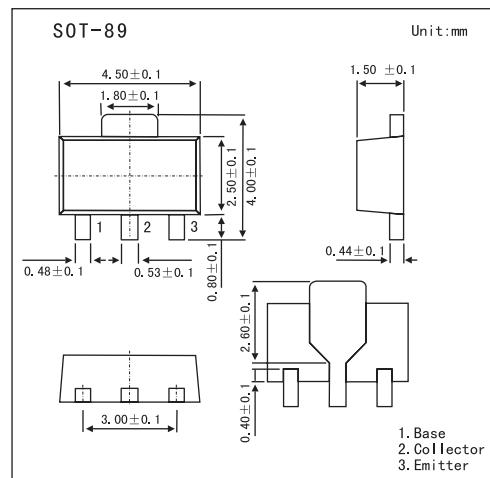


**Silicon PNP Epitaxial****2SA1734****■ Features**

- Low saturation voltage:  $V_{CE(sat)} = -0.5$  V (max) ( $I_C = -700$  mA).
- High speed switching time:  $t_{stg} = 0.2\mu s$  (typ.).
- Small flat package.
- $PC = 1.0$  to  $2.0$  W (mounted on ceramic substrate).

**■ Absolute Maximum Ratings  $T_a = 25^\circ C$** 

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	-40	V
Collector-emitter voltage	$V_{CEO}$	-30	V
Emitter-base voltage	$V_{EBO}$	-6	V
Collector current	$I_C$	-2	A
Base current	$I_B$	-1.2	A
Collector power dissipation	$P_C$	500	mW
	$P_C^*$	1000	
Junction temperature	$T_j$	150	°C
Storage temperature range	$T_{stg}$	-55 to +150	°C

\* Mounted on ceramic substrate (250 mm<sup>2</sup> X 0.8 t)

**2SA1734**

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> = -40 V, I <sub>E</sub> = 0			-0.1	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> = -6 V, I <sub>C</sub> = 0			-0.1	μA
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> = -10 mA, I <sub>B</sub> = 0	-50			V
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> = -2 V, I <sub>C</sub> = -100 mA	120		400	
		V <sub>CE</sub> = -2 V, I <sub>C</sub> = -1.0 A	40			
Collector-emitter saturation voltage	V <sub>CE</sub> (sat)	I <sub>C</sub> = -700 mA, I <sub>B</sub> = -35 mA			-0.5	V
Base-emitter saturation voltage	V <sub>BE</sub> (sat)	I <sub>C</sub> = -700 mA, I <sub>B</sub> = -35 mA			-1.2	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> = -2 V, I <sub>C</sub> = -100 mA	100			MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0, f = 1 MHz	16			pF
Turn-on time	t <sub>on</sub>	 -I <sub>B1</sub> = I <sub>B2</sub> = 35 mA, DUTY CYCLE ≤ 1%		0.1		μs
Storage time	t <sub>stg</sub>			0.2		μs
Fall time	t <sub>f</sub>			0.1		μs

## ■ Marking

Marking	LB
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